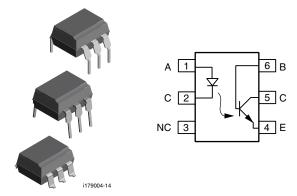


**Vishay Semiconductors** 

# **Optocoupler, Phototransistor Output, with Base Connection**



### DESCRIPTION

The 4N25 family is an Industry Standard Single Channel Phototransistor Coupler. This family includes the 4N25, 4N26, 4N27, 4N28. Each optocoupler consists of gallium arsenide infrared LED and a silicon NPN phototransistor.

These couplers are Underwriters Laboratories (UL) listed to comply with a 5300 V<sub>RMS</sub> isolation test voltage. This isolation performance is accomplished through special Vishay manufacturing process.

Compliance to DIN EN 60747-5-2 (VDE 0884)/ DIN EN 60747-5-5 pending partial discharge isolation specification is available by ordering option 1.

These isolation processes and the Vishay ISO9001 quality program results in the highest isolation performance available for a commercial plastic phototransistor optocoupler.

The devices are also available in lead formed configuration suitable for surface mounting and are available either on tape and reel, or in standard tube shipping containers.

#### Note

For additional design information see application note 45 normalized curves

### **FEATURES**

- Isolation test voltage 5000 V<sub>BMS</sub>
- · Interfaces with common logic families
- Input-output coupling capacitance < 0.5 pF</li>
- · Industry standard dual-in-line 6-pin package
- Compliant to RoHS Directive 2002/95/EC and in accordance to WEEE 2002/96/EC

#### APPLICATIONS

- AC mains detection
- Reed relay driving
- Switch mode power supply feedback
- Telephone ring detection
- Logic ground isolation
- · Logic coupling with high frequency noise rejection

### AGENCY APPROVALS

- UL file no. E52744
- cUL tested to CSA 22.2 bulletin 5A
- DIN EN 60747-5-2 (VDE 0884)/DIN EN 60747-5-5 (pending), available with option 1
- BSI: EN 60065, EN 60950-1
- FIMKO
- CQC

ORDERING INFORMATION					
4 N 2 x	- x	0 #	T   TAPE   AND   REEL	S2 mm        Option 6          s2 mm        10.16 mm          otion 7        Option 9          8 mm        8 mm typ.	
AGENCY CERTIFIED/PACKAGE	CTR (%)				
UL, cUL, BSI, FIMKO	≥20 ≥10				
DIP-6	4N25-X000	-	4N27-X000	-	
DIP-6, 400 mil, option 6	4N25-X006	4N26-X006	-	-	
SMD-6, option 7	4N25-X007T	-	4N27-X007	-	
SMD-6, option 9	4N25-X009T <sup>(1)</sup>	4N26-X009T <sup>(1)</sup>	4N27-X009T <sup>(1)</sup>	4N28-X009T <sup>(1)</sup>	
VDE, UL, cUL, BSI, FIMKO	2	20	≥.	10	
DIP-6	4N25-X001	4N26-X001	-	4N28-X001	
DIP-6, 400 mil, option 6	4N25-X016	4N26-X016	-	-	
SMD-6, option 7	4N25-X017T <sup>(1)</sup>	4N26-X017T <sup>(1)</sup>	4N27-X017T	-	

Additional options may be possible, please contact sales office. <sup>(1)</sup> Also available in tubes; do not put T on end.

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ABSOLUTE MAXIMUM RATI	NGS (T <sub>amb</sub> = 25 °C, unless ot	herwise specifie	ed)		
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT	
INPUT					
Reverse voltage		V <sub>R</sub>	6	V	
Forward current		I <sub>F</sub>	60	mA	
Surge current	t ≤ 10 µs	I <sub>FSM</sub>	2.5	А	
Power dissipation		P <sub>diss</sub>	70	mW	
OUTPUT					
Collector emitter breakdown voltage		V <sub>CEO</sub>	70	V	
Emitter base breakdown voltage		V <sub>EBO</sub>	7	V	
Collector current		Ι <sub>C</sub>	50	mA	
Collector peak current	$t_p/T = 0.5, t_p \le 10 \text{ ms}$	I <sub>CM</sub>	100	mA	
Output power dissipation		P <sub>diss</sub>	150	mW	
COUPLER					
Isolation test voltage		V <sub>ISO</sub>	5000	V <sub>RMS</sub>	
Creepage distance			≥7	mm	
Clearance distance			≥7	mm	
Isolation thickness between emitter and detector			≥ 0.4	mm	
Comparative tracking index	DIN IEC 112/VDE0303, part 1		≥ 175		
Isolation resistance	$V_{IO} = 500 \text{ V}, \text{ T}_{amb} = 25 ^{\circ}\text{C}$	R <sub>IO</sub>	≥ 10 <sup>12</sup>	Ω	
ISUIALIUTI TESISLATICE	$V_{IO} = 500 \text{ V}, \text{ T}_{amb} = 100 ^{\circ}\text{C}$	R <sub>IO</sub>	≥ 10 <sup>11</sup>	Ω	
Storage temperature		T <sub>stg</sub>	- 55 to + 150	°C	
Operating temperature		T <sub>amb</sub>	- 55 to + 100	°C	
Junction temperature		Тį	100	°C	
Soldering temperature <sup>(1)</sup>	2 mm from case, ≤ 10 s	T <sub>sld</sub>	260	°C	

Notes

Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of this document. Exposure to absolute maximum ratings for extended periods of the time can adversely affect reliability.
 (1) Refer to reflow profile for soldering conditions for surface mounted devices (SMD). Refer to wave profile for soldering conditions for through hole devices (DIP).

PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
INPUT						<u>.</u>	
Forward voltage <sup>(1)</sup>	I <sub>F</sub> = 50 mA		V <sub>F</sub>		1.36	1.5	V
Reverse current <sup>(1)</sup>	V <sub>R</sub> = 3.0 V		I <sub>R</sub>		0.1	100	μA
Capacitance	V <sub>R</sub> = 0 V		Co		25		pF
OUTPUT					•		
Collector base breakdown voltage <sup>(1)</sup>	I <sub>C</sub> = 100 μA		BV <sub>CBO</sub>	70			V
Collector emitter breakdown voltage <sup>(1)</sup>	I <sub>C</sub> = 1.0 mA		BV <sub>CEO</sub>	30			V
Emitter collector breakdown voltage (1)	I <sub>E</sub> = 100 μA		BV <sub>ECO</sub>	7			V
	V <sub>CE</sub> = 10 V, (base open)	4N25			5	50	nA
(		4N26			5	50	nA
I <sub>CEO</sub> (dark) <sup>(1)</sup>		4N27			5	50	nA
		4N28			10	100	nA
I <sub>CBO</sub> (dark) <sup>(1)</sup>	V <sub>CB</sub> = 10 V, (emitter open)				2.0	20	nA
Collector emitter capacitance	$V_{CE} = 0$		C <sub>CE</sub>		6.0		pF
COUPLER						-	
Isolation test voltage (1)	Peak, 60 Hz		V <sub>IO</sub>	5000			V
Saturation voltage, collector emitter	$I_{CE} = 2.0 \text{ mA}, I_F = 50 \text{ mA}$		V <sub>CE(sat)</sub>			0.5	V
Resistance, input output (1)	V <sub>IO</sub> = 500 V		R <sub>IO</sub>	100			GΩ
Capacitance, input output	f = 1 MHz		C <sub>IO</sub>		0.5		pF

#### Notes

Minimum and maximum values are testing requirements. Typical values are characteristics of the device and are the result of engineering evaluation. Typical values are for information only and are not part of the testing requirements. JEDEC registered values are 2500 V, 1500 V, 1500 V and 500 V for the 4N25, 4N26, 4N27, and 4N28 respectively.

(1)



# 4N25-X, 4N26-X, 4N27-X, 4N28-X

# **Vishay Semiconductors**

CURRENT TRANSFER RATIO (T <sub>amb</sub> = 25 °C, unless otherwise specified)								
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT	
I <sub>C</sub> /I <sub>F</sub>	V <sub>CE</sub> = 10 V, I <sub>F</sub> = 10 mA	4N25	CTR <sub>DC</sub>	20	50		%	
		4N26	CTR <sub>DC</sub>	20	50		%	
		4N27	CTR <sub>DC</sub>	10	30		%	
		4N28	CTR <sub>DC</sub>	10	30		%	

Note

• Indicates JEDEC registered values.

SWITCHING CHARACTERISTICS ( $T_{amb} = 25 \text{ °C}$ , unless otherwise specified)							
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT	
Rise time	$V_{CC}$ = 5 V, $I_F$ = 10 mA, $R_L$ = 100 $\Omega$	t <sub>r</sub>		2.0		μs	
Fall time	$V_{CC}$ = 5 V, $I_F$ = 10 mA, $R_L$ = 100 $\Omega$	t <sub>f</sub>		2.0		μs	

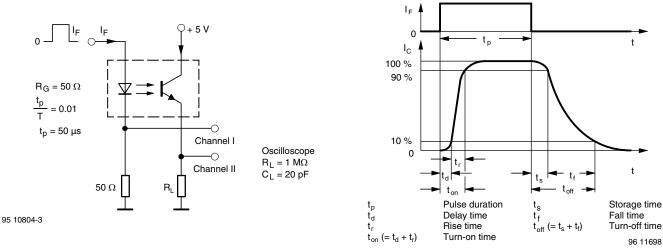


Fig. 1 - Test Circuit, Non-Saturated Operation

Fig. 2 - Switching Times

### TYPICAL CHARACTERISTICS (T<sub>amb</sub> = 25 °C, unless otherwise specified)

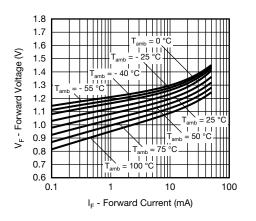


Fig. 3 - Forward Voltage vs. Forward Current

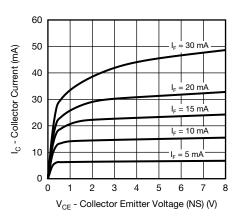


Fig. 4 - Collector Current vs. Collector Emitter Voltage (NS)



# 4N25-X, 4N26-X, 4N27-X, 4N28-X

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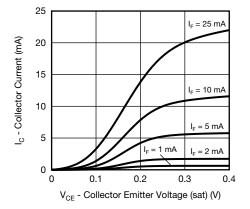


Fig. 5 - Collector Current vs. Collector Emitter Voltage (sat)

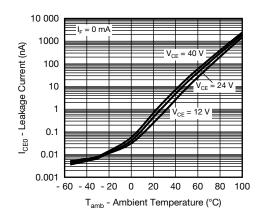


Fig. 6 - Leakage Current vs. Ambient Temperature

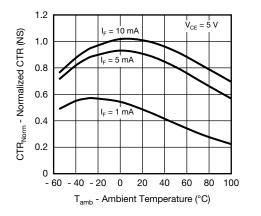


Fig. 7 - Normalized CTR (NS) vs. Ambient Temperature

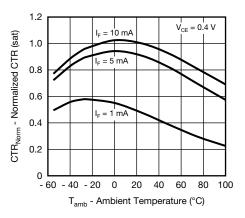


Fig. 8 - Normalized CTR (sat) vs. Ambient Temperature

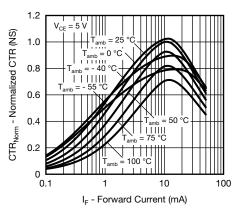


Fig. 9 - Normalized CTR (NS) vs. Forward Current

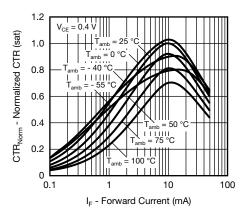


Fig. 10 - Normalized CTR (sat) vs. Forward Current

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4 For technical questions, contact: <u>optocoupleranswers@vishay.com</u> Document Number: 81864

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# 4N25-X, 4N26-X, 4N27-X, 4N28-X

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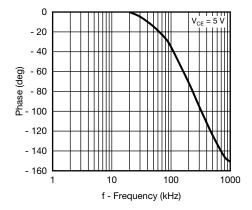


Fig. 11 - CTR Frequency vs. Phase Angle

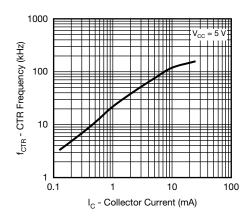


Fig. 12 - CTR Frequency vs. Collector Current

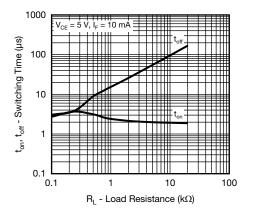
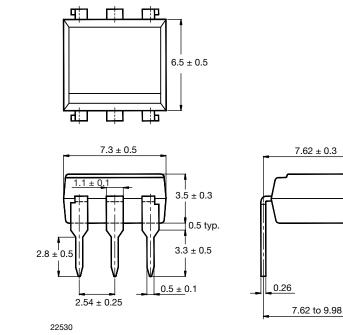


Fig. 13 - Switching Time vs. Load Resistance



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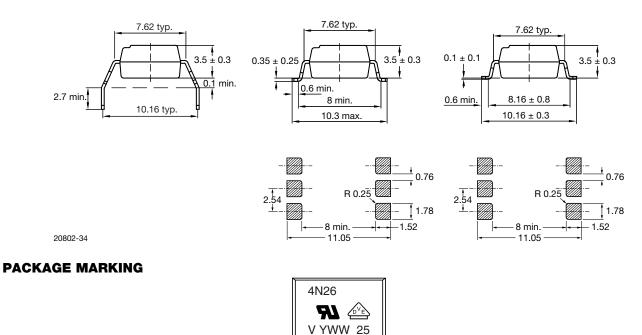
### **PACKAGE DIMENSIONS** in millimeters



Option 6

Option 7

Option 9



#### Notes

- VDE logo is only marked on option 1 parts. Option information is not marked on the part.
- Tape and reel suffix (T) is not part of the package marking.



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